

# Gallardo-Hernández Salvador

## List of Publications by Year in descending order

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55  
papers

373  
citations

933447

10  
h-index

940533

16  
g-index

55  
all docs

55  
docs citations

55  
times ranked

471  
citing authors

#	ARTICLE	IF	CITATIONS
1	Hyperbolic-tangent composition-graded In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs (100) structures grown by molecular beam epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2022, 142, 106486.	4.0	0
2	Study of the surface chemistry, surface morphology, optical, and structural properties of InGaN thin films deposited by RF magnetron sputtering. <i>Applied Surface Science</i> , 2022, 586, 152795.	6.1	4
3	Cubic In <sub>x</sub> Ga <sub>1-x</sub> N/GaN quantum wells grown by Migration Enhanced Epitaxy (MEE) and conventional Molecular Beam Epitaxy (MBE). <i>Journal of Alloys and Compounds</i> , 2022, 921, 165994.	5.5	4
4	Indium incorporation at In <sub>x</sub> Ga <sub>1-x</sub> N relaxed self-assembled nanostructures on Si substrates. <i>Materials Science in Semiconductor Processing</i> , 2022, 150, 106946.	4.0	0
5	Unveiling the influence of ZnTe and Te layers as part of the back-contact on CdTe solar cells performance. <i>AIP Advances</i> , 2021, 11, .	1.3	5
6	Study of Atomic Hydrogen Concentration in Grain Boundaries of Polycrystalline Diamond Thin Films. <i>Applied Sciences (Switzerland)</i> , 2021, 11, 3990.	2.5	11
7	Interference and electro-optical effects in cubic GaN/GaAs heterostructures prepared by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2020, 128, 125706.	2.5	3
8	Study of the heavily p-type doping of cubic GaN with Mg. <i>Scientific Reports</i> , 2020, 10, 16858.	3.3	25
9	Optical studies of nitrogen plasma for molecular beam epitaxy of InN. <i>Journal of Applied Physics</i> , 2020, 128, 215304.	2.5	5
10	Characterization of n-GaN / p-GaAs NP heterojunctions. <i>Superlattices and Microstructures</i> , 2019, 136, 106298.	3.1	10
11	Growth Mechanism and Properties of Self-Assembled InN Nanocolumns on Al Covered Si(111) Substrates by PA-MBE. <i>Materials</i> , 2019, 12, 3203.	2.9	4
12	Structural and optical study of alternating layers of In and GaAs prepared by magnetron sputtering. <i>Universitas Scientiarum</i> , 2019, 24, 523-542.	0.4	1
13	Sol-gel synthesis of Ag-loaded TiO <sub>2</sub> -ZnO thin films with enhanced photocatalytic activity. <i>Journal of Alloys and Compounds</i> , 2019, 779, 908-917.	5.5	53
14	Voc enhancement of a solar cell with doped Li + -PbS as the active layer. <i>Superlattices and Microstructures</i> , 2018, 118, 137-144.	3.1	10
15	High cubic phase purity and growth mechanism of cubic InN thin-films by Migration Enhanced Epitaxy. <i>Thin Solid Films</i> , 2018, 647, 64-69.	1.8	3
16	CdS/CdTe Heterostructures for Applications in Ultra-Thin Solar Cells. <i>Materials</i> , 2018, 11, 1788.	2.9	15
17	SIMS depth profiling of "frozen"™ samples: in search of ultimate depth resolution regime. <i>Surface and Interface Analysis</i> , 2017, 49, 145-148.	1.8	2
18	In <sub>x</sub> Ga <sub>1-x</sub> As obtained from independent target via co-sputtering deposition. <i>Journal of Physics: Conference Series</i> , 2017, 850, 012013.	0.4	0

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19	Enhancement of CdS/CdTe solar cells by the interbuilding of a nanostructured Te-rich layer. Materials Research Express, 2017, 4, 086403.	1.6	14
20	Structural and optical characterization of GaAs and InGaAs thin films deposited by RF magnetron sputtering. Optik, 2017, 145, 608-616.	2.9	7
21	Effects of growth temperature on the incorporation of nitrogen in GaNAs layers. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, .	1.2	1
22	Up and Down Conversion Photoluminescence from Er, Yb and Li Doped $Y_2O_3$ Phosphors and Composites Films with PMMA. ECS Journal of Solid State Science and Technology, 2016, 5, R129-R135.	1.8	12
23	Electrical, Optical and Structural Properties of $SnO_2$ :Sb:F Thin Films Deposited from $Sn(acac)_2$ by Spray Pyrolysis. ECS Journal of Solid State Science and Technology, 2016, 5, Q101-Q107.	1.8	8
24	Magnetization in AlIBV semiconductor heterostructures with the depletion layer of manganese. Low Temperature Physics, 2015, 41, 157-159.	0.6	1
25	On the gaps observed in high resolution x-ray diffraction scans and the wiggles in reciprocal space maps of high quality crystalline samples. , 2015, , .		0
26	Formation of self-organized nano-surfaces on III-V semiconductors by low energy oxygen ion bombardment. Materials Science in Semiconductor Processing, 2015, 37, 190-198.	4.0	5
27	Study of interference effects on the photoluminescence of AlGaIn/GaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 365-368.	0.8	2
28	Graded composition $Cd_xZn_{1-x}Te$ films grown by Isothermal Close Space Sublimation technique. Solar Energy Materials and Solar Cells, 2015, 138, 17-21.	6.2	14
29	As <sub>4</sub> overpressure effects on the phase purity of cubic GaN layers grown on GaAs substrates by RF-MBE. Applied Surface Science, 2015, 353, 588-593.	6.1	15
30	Chemical analysis of obsidian by a SIMS/EDX combined system. Nuclear Instruments & Methods in Physics Research B, 2015, 343, 153-157.	1.4	4
31	Characterization of Lanthanum-Aluminum Oxide Thin Films Deposited by Spray Pyrolysis. ECS Journal of Solid State Science and Technology, 2014, 3, N1-N6.	1.8	5
32	Reconstruction of original indium distribution in InGaAs quantum wells from experimental SIMS depth profiles. Physica B: Condensed Matter, 2014, 453, 53-58.	2.7	12
33	Effect of the immersion in CdCl <sub>2</sub> and annealing on physical properties of CdS:F films grown by CBD. Journal of Physics and Chemistry of Solids, 2013, 74, 611-615.	4.0	24
34	MBE growth and characterization of (100) and (631)-oriented modulation doped AlGaAs/GaAs heterostructures. Journal of Crystal Growth, 2013, 378, 88-91.	1.5	1
35	Two orders of magnitude reduction in the temperature dependent resistivity of $Ga_{1-x}Mn_xAs$ grown on (6 3 1) GaAs insulating substrates. , 2013, , .		1
36	Optical and electrical study of cap layer effect in QHE devices with double-2DEG. Materials Research Society Symposia Proceedings, 2013, 1617, 31-36.	0.1	1

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37	Self-assembly of compositionally modulated Ga <sup>x</sup> Mn <sub>x</sub> As multilayers during molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	8
38	Study of structural properties of cubic InN films on GaAs(001) substrates by molecular beam epitaxy and migration enhanced epitaxy. Journal of Applied Physics, 2013, 113, 214308.	2.5	11
39	Group III-nitrides nanostructures. , 2012, , .		0
40	Electrical and optical properties of Si doped GaAs (631) layers studied as a function of the growth temperature. Journal of Crystal Growth, 2012, 347, 77-81.	1.5	4
41	SIMS depth profiling of semiconductor interfaces: Experimental study of depth resolution function. Surface and Interface Analysis, 2011, 43, 1277-1281.	1.8	3
42	Photoreflectance study of GaMnAs layers grown by MBE. Journal of Crystal Growth, 2011, 323, 344-347.	1.5	2
43	Nitrogen Incorporation in Al <sub>2</sub> O <sub>3</sub> Thin Films Prepared by Pulsed Ultrasonic Sprayed Pyrolysis. ECS Transactions, 2009, 25, 179-186.	0.5	3
44	Study of the oxygen incorporation in Al <sub>0.2</sub> Ga <sub>0.3</sub> In <sub>0.5</sub> P:Be layers grown by MBE employing a P-cracker cell. Journal of Crystal Growth, 2009, 311, 1650-1654.	1.5	3
45	Study of AlGaAs/GaAs quantum wells grown by molecular beam epitaxy on GaAs substrates subjected to different treatments. Journal of Crystal Growth, 2009, 311, 1666-1670.	1.5	2
46	Cesium ion sputtering with oxygen flooding: Experimental SIMS study of work function change. Applied Surface Science, 2008, 254, 4961-4964.	6.1	9
47	SIMS characterization of segregation in InAs/GaAs heterostructures. Applied Surface Science, 2008, 255, 1341-1344.	6.1	9
48	SIMS depth profiling analysis of halogens in CdTe/CdS/TSO solar cells using Cs <sub>2</sub> M <sup>+</sup> cluster ions. Applied Surface Science, 2008, 255, 1423-1426.	6.1	5
49	Optical characterization of InAs -layers grown by MBE at different substrate temperatures. Microelectronics Journal, 2008, 39, 1284-1285.	2.0	1
50	Ionization probability of sputtered particles as a function of their energy. Applied Surface Science, 2008, 254, 3801-3807.	6.1	7
51	Probability of ionization of sputtered particles as a function of their energy. Applied Surface Science, 2008, 254, 2059-2066.	6.1	8
52	Critical distance for secondary ion formation: Experimental SIMS measurements. Applied Surface Science, 2008, 255, 877-879.	6.1	2
53	Depth-profile analysis of nanostructures by SIMS: Depth resolution function. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 895-898.	0.6	7
54	SIMS Study of Modern Semiconductor Heterostructures.. , 2006, , .		0

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55	Effects of heavy Si doping on the structural and optical properties of n-GaN/AlN/Si(111) heterostructures. Materials Research Express, 0, , .	1.6	7